抵抗変化（電子スピン共鳴）を導入することにより、イオン・インプラントされたSi: P系における抵抗特性が変化する。この研究は、物理の基礎的な研究であり、多くの研究者により行われています。

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Resistance changes induced by electron-spin resonance in ion-implanted Si:P system

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The ESR-induced changes in the dc resistance, $\Delta \rho/\rho_{\text{ESR}}$, of P-ion-implanted silicon have been observed for the first time. The transfer of absorbed Zeeman energy at liquid-He temperature has been investigated. The $\Delta \rho/\rho_{\text{ESR}}$ signals observed were a narrow line with a $g$ value of 1.9988 for light-dose implantation and a new broad line with a little larger $g$ value for heavy-dose implantation. The line shape of these $\Delta \rho/\rho_{\text{ESR}}$ signals was Lorentzian as well as the ESR signal, but the linewidth $\Delta H_{\text{ss}}$ of the broad $\Delta \rho/\rho_{\text{ESR}}$ signal was about 10 times as broad as the ESR linewidth. It is suggested that the anomalously broad line of $\Delta \rho/\rho_{\text{ESR}}$ originates from the transfer of the Zeeman energy absorbed by the localized donor electrons at the tail regions with low donor concentration ($5 \times 10^{15} < N_D < 1.5 \times 10^{16}$ P/cm$^3$) to the layer with intermediate donor concentration ($1.5 \times 10^{15} < N_D < 3.7 \times 10^{16}$ P/cm$^3$) where the resistance changes take place. This transfer is caused by the existence of the peak regions with high donor concentration ($N_D \geq 2 \times 10^{18}$ P/cm$^3$) which act as Zeeman energy absorbers.

PACS numbers: 61.80.Jh, 76.30.Pk, 72.20.Jv

I. INTRODUCTION

The ESR-induced changes in the dc electrical resistance, $\Delta \rho/\rho_{\text{ESR}}$, have been measured by many workers$^1$-$^4$ for $n$-type semiconductors (e.g., InSb, Si, and Ge) at low temperature to investigate the spin-dependent conductivity, the relaxation mechanism of the Zeeman energy, and the electronic state of donor atoms. In this method, the static magnetic field is slowly swept at a constant microwave frequency in the same way as the usual ESR method, and the change in resistance is detected at the resonant field corresponding to the ESR signal. It was shown by Guéron and Solomon$^1$ that for very small samples the method of measuring $\Delta \rho/\rho_{\text{ESR}}$ should be much more sensitive than the usual ESR method. Therefore, it is useful to apply the $\Delta \rho/\rho_{\text{ESR}}$ method to ion-implanted semiconductors which contain a small number of spins.$^5$

For bulk Si : P (Si doped uniformly with phosphorus), many investigations have been done at the intermediate concentration region ($1.5 \times 10^{16} < N_D < 3.7 \times 10^{16}$ P/cm$^3$) and the high- (I) concentration region ($3.7 \times 10^{16} < N_D < 2 \times 10^{18}$ P/cm$^3$).$^4$ It has been impossible to observe the $\Delta \rho/\rho_{\text{ESR}}$ at the low-concentration region ($N_D < 1.5 \times 10^{17}$ P/cm$^3$) and high- (II) concentration region ($N_D > 2 \times 10^{18}$ P/cm$^3$).$^2$-$^4$ The energy reservoir of interest is considered to be the kinetic-energy system of the delocalized donor electrons coupled to the donor electron spins by the spin-orbit interaction.$^1$-$^5$ The power fed by the donor spins increases the kinetic energy of the electrons, and this is detected by an increase in the mobility, that is, a decrease in dc resistance.

In previous papers,$^6$-$^8$ the ESR study at 77 K was performed on an ion-implanted Si : P system, in which the phosphorus distribution is nearly Gaussian, as shown in Fig. 1. In the system investigated, delocalized donor electrons (conduction electrons) move around very rapidly in the whole implanted layer during the virtual spin-lattice relaxation time $\tau_b(x_i)$ of the $i$th layer $\Delta x_i$ between $x_i$ and $x_i + \Delta x_i$. That is, the implanted layer is much thinner than the spin mean free path, $\delta_{\text{eff}} = (2/3)\lambda \tau_b^{1/2}$ = several $\mu$m, where the $v_F$ is the mean value of the Fermi velocity, $\lambda$ is the electronic mean free path, and $\tau_b$ is the mean value of $\tau_b(x_i)$. Therefore, an effective spin-lattice relaxation time $T_{\text{eff}}$ of the implanted layer is an average of $\tau_b(x_i)$ over the whole implanted layer and can be determined experimentally from the linewidth $\Delta H_{\text{ss}}$ of the Lorentzian ESR spectrum as $T_{\text{eff}} = 2/\gamma \Delta H_{\text{ss}}$.$^7$ If donor electrons were completely localized and there were no energy transfers, $\tau_b(x_i)$ would be unchanged and the ESR linewidth would be Gaussian because of the superposition of signals with different linewidths, $\Delta H_{\text{ss}} = 2/\gamma \Delta \tau_b(x_i)$. $T_{\text{eff}}$ is thought to be dominated by a extremely thin layer with the shortest $\tau_b(x_i)$.$^7$-$^8$

At liquid-helium-temperature (LHeT) regions, the system becomes different from that at 77 K; i.e., two kinds of layers coexist in the ion-implanted Si : P system, as shown in Fig. 1. One is the layer at peak regions of the impurity profile, where the donor concentrations are higher than that for the metal-insulator (Mott) transition ($N_D = 3.7 \times 10^{14}$ P/cm) and delocalized donor electrons behave like free electrons.$^5$ Thus, the layer shows metallic conductance. The other is the layer at the tail regions, where the donor concentrations are lower than $N_D$ and the donor electrons are completely localized.$^6$ Thus, the layer becomes an insulator.

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at low temperature. The importance of the Zeeman energy transfer between these two kinds of layers seems to be unclear in ion-implanted semiconductors.

In this paper, we investigate the relaxation mechanism at LHET through the transfer of absorbed Zeeman energy between two kinds of layers by the methods of both $\Delta \rho/\rho \mid_{\text{ERS}}$ and ESR. We believe that this is the first observation of $\Delta \rho/\rho \mid_{\text{ERS}}$ in ion-implanted samples. The origin and the mechanism of $\Delta \rho/\rho \mid_{\text{ERS}}$ are discussed.

II. EXPERIMENTAL PROCEDURE

Phosphorus-ion implantation in silicon was done at an energy of 200 keV with doses of $1 \times 10^{14}$ to $3 \times 10^{15}$ P/cm$^2$ and at an energy of 50 keV with doses of $1 \times 10^{14}$ to $1 \times 10^{15}$ P/cm$^2$ at room temperature. The samples were annealed in a vacuum of about $10^{-6}$ Torr at 900°C for 15 min in order to obtain substitutional P in nearly damage-free Si (ion-implanted Si : P). For 200-keV P$^+$, the average projected range $R_p$ and the projected standard deviation of the range $\sigma$ are about 2500 and 800 Å, respectively, and for 50-keV P$^+$ these are 600 and 250 Å, respectively.

Contacts were formed by depositing and alloying the Au-Sb (0.5 wt% antimony) to measure the dc resistance. At room temperature and 77 K, the $I$-$V$ characteristic was Ohmic, but at LHET (1.6 - 4.2 K), only about one-third of the samples showed Ohmic character.

The dc resistance changes induced by ESR, $\Delta \rho/\rho \mid_{\text{ERS}}$, was obtained by measuring the changes of the dc voltage across the sample at the microwave frequency of 9 GHz at 4.2 and 1.6 K. The spectrometers used were of a balanced mixer type. Samples were mounted on a Teflon holder at the center of the TE$_{101}$ rectangular cavity, where the oscillating magnetic field was strongest. The microwave power was modulated in a square waveform with a frequency of 10 or 100 kHz. The signal corresponding to the change of the voltage across the sample due to ESR, $\Delta \rho/\rho \mid_{\text{ERS}}$, or due to only microwave irradiation at off resonance, $\Delta \rho/\rho \mid_{\text{off}}$, was phase detected through a lock-in detector, and, in some cases, an accumulator was used to improve the S/N ratio. The $\Delta \rho/\rho \mid_{\text{off}}$ is dependent on the electronic state of donor electrons. Microwave power and electrical field across the sample were varied from 0.4 to 50 mW and from 20 mV/cm to 10 V/cm, respectively. The bulk Si : P doped at $1.8 \times 10^{18}$ P/cm$^2$ was also measured as a standard sample for determining a sign of the resistance changes.

Since the cavity $Q$ value was much lower for the $\Delta \rho/\rho \mid_{\text{ERS}}$ measurement, it was difficult to obtain the ESR signal with a good S/N ratio. Therefore, both a balanced mixer type and a conventional reflection-type ESR spectrometers at 9 GHz were employed for ESR measurements at 4.2 and 1.6 K. Cavities used were of the type of rectangular TE$_{101}$ or cylindrical TE$_{111}$. Several samples were mounted at the bottom of the cavity to improve the S/N ratio further.

III. EXPERIMENTAL RESULTS

In the case of the bulk Si : P with the donor concentration of $1.8 \times 10^{18}$ P/cm$^2$, the signs of $\Delta \rho/\rho \mid_{\text{ERS}}$ and $\Delta \rho/\rho \mid_{\text{off}}$ were negative. A negative sign means the decrease of electrical resistance, which was confirmed by measuring directly a change of the voltage across the sample. The linewidth $\Delta H_{1/2}$ of $\Delta \rho/\rho \mid_{\text{ERS}}$ was completely equal to the ESR linewidth $\Delta H_{1/2} (\approx \sqrt{3} \Delta H_{\text{sat}})$, as shown in Fig. 2(a).

The ESR and the $\Delta \rho/\rho \mid_{\text{ERS}}$ signals observed in ion-implanted Si : P showed a single Lorentzian line shape as illustrated in Figs. 2(b) and 2(c). As expected, the $\Delta \rho/\rho \mid_{\text{ERS}}$ method was much more sensitive for ion-implanted Si : P than the usual ESR. All implanted samples showed a negative sign for $\Delta \rho/\rho \mid_{\text{ERS}}$ and a positive sign for $\Delta \rho/\rho \mid_{\text{off}}$. These behaviors are the same as those of bulk Si : P with the donor concentrations above the critical concentration for the metal-insulator transition ($3.7 \times 10^{18}$ P/cm$^2$).

The observed $\Delta \rho/\rho \mid_{\text{ERS}}$ signals showed two kinds of lines. For ion-implanted Si : P with 200-keV P and a
dose of $3 \times 10^{14}$ cm$^{-2}$, the $\Delta \rho/\rho |_{\text{ESR}}$ signal was a narrow line with a $g$ value of 1.9988, as shown in Fig. 2(b). The narrow line agrees with the ESR line and is the same with the $\Delta \rho/\rho |_{\text{ESR}}$ observed in bulk Si:P. However, for ion-implanted Si:P samples with a higher effective donor concentration $N_D^{*}$, a new broad signal of $\Delta \rho/\rho |_{\text{ESR}}$ was observed. The signal showed a much broader line with a larger $g$ value than that of the ESR signal as shown in Figs. 2(c) and 3. The broader lines of $\Delta \rho/\rho |_{\text{ESR}}$ have a width of between 15 and 20 G, while the ESR linewidth $\Delta H_{1/2}$ has much smaller value as shown in Fig. 3. Therefore, the new signal is found not to be induced by the ESR of delocalized electrons at peak regions. It should be also noted that the line shape is Lorentzian though it is a little asymmetric. At a $N_D^{*}$ of $8.5 \times 10^{18}$ P/cm$^3$, both the narrow and the broad lines of $\Delta \rho/\rho |_{\text{ESR}}$ were observed. The linewidth $\Delta H_{1/2}$ of $\Delta \rho/\rho |_{\text{ESR}}$ decreases with increasing $N_D^{*}$ above $8.5 \times 10^{18}$ P/cm$^3$. No signal of $\Delta \rho/\rho |_{\text{ESR}}$ was detected at a $N_D^{*}$ of $8.5 \times 10^{18}$ P/cm$^3$.

The ESR linewidth of ion-implanted Si:P at LHeT agrees with that of bulk Si:P above an $N_D^{*}$ of about $2 \times 10^{19}$ P/cm$^3$, as can be seen in Fig. 3. However, below $2 \times 10^{19}$ P/cm$^3$, the former is broader than the latter. The difference seems to arise from the existence of localized donor electrons at the tail regions, i.e., the energy transfer from the tail regions to the peak regions is much slower than the inverse relaxation rate $\tau_{\text{rel}}$ of the peak regions.

The dependence of the intensity of $\Delta \rho/\rho |_{\text{ESR}}$ on $N_D^{*}$ is shown in Fig. 4. The intensity for the narrow line decreases with increasing $N_D^{*}$, which agrees with the results in bulk Si:P. On the other hand, the intensity for the broad line seems to increase with increasing $N_D^{*}$.

IV. DISCUSSION

The anomalously broad line of $\Delta \rho/\rho |_{\text{ESR}}$ is not observed in bulk Si:P but in ion-implanted Si:P. The latter differs from the former in having the tail regions with localized donor spins, as shown in Fig. 1. The layer with low, intermediate, high (I), and high (II) concentration regions of donor atoms are hereafter called LR, IR, HR(I), and HR(II), respectively.

The questions now are what is the origin of ESR which causes the broad line, and how are the resistance...
is characteristic of fast energy transfer induced by the existence of HR(II) \((N_D < 2 \times 10^{18} \text{ P/cm}^3)\) which has the shortest \(\tau_0(x_i)\) and so acts as a Zeeman energy absorber.

At HR(I) or HR(II) and HR(III), an effective spin-lattice relaxation time \(T_{\text{rel}}\) is determined as an average since the spin mean free path \(\delta_{\text{rel}}\), is much greater than the thickness of HR. Therefore, the ion-implanted Si : P system is considered to be a system where the fast relaxing centers with the relaxing rate of \(T_{\text{rel}}^{-1}\) are added to the surface of the layer of IR. If so, it will depend on the rate of energy transfer to the surface whether the broad line appears.

For the ion-implanted Si with 200-keV P and a dose of \(1 \times 10^{13} \text{ P/cm}^3\) (sample No. 1), a block diagram for the relaxation process of the absorbed Zeeman energy is shown in Fig. 5(a). It means that \(T_{\text{rel}}\) is determined at HR and that most of the Zeeman energy absorbed there is relaxed into the lattice system at the layer with the shortest \(\tau_0(x_i)\) in HR(III). At relatively high temperature \((7700000000)\), \(T_{\text{rel}}^{-1}\) is determined over the whole implanted layer as follows:

\[
T_{\text{rel}}^{-1} = \left( \int_0^\infty \tau_0(x)^{-1} N_p(x) \, dx \right)^{-1} + \tau_0^{-1},
\]

where \(N_p(x)\) is the depth profile of P, \(\tau_0\) is the relaxing time due to the phonon-dependent process and is assumed to be independent of \(N_p(x)\) at a certain temperature. Equation (1) shows that the implanted layer is one Zeeman system since \(\delta_{\text{rel}}\) is much greater than the thickness of the implanted layer and that the Zeeman energy of each delocalized electron flows into the lattice through the many relaxing paths of

\[
T_{\text{rel}}(x_i)^{-1} = \frac{\tau_0(x_i)^{-1} N_p(x_i) \Delta x_i}{\int \sum N_p(x) \Delta x_i} \quad (i = 1, 2, \ldots, n).
\]

The energy relaxed at the \(i\)th layer, \(\Delta x_i\), is proportional to the value of \(T_{\text{rel}}(x_i)^{-1}\) in Eq. (2). Although the rate of energy transfer greatly differs between HR and IR, the Zeeman energy absorbed at IR is thought to be

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**TABLE I. The mean values applied for four layers.**

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<tr>
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<th>HR(II)</th>
<th>HR(I)</th>
<th>IR</th>
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<tr>
<td>Concentration of donors ((\text{cm}^{-3}))</td>
<td>(n_1 = 3 \times 10^{19})</td>
<td>(n_2 = 6 \times 10^{18})</td>
<td>(n_3 = 2 \times 10^{18})</td>
<td>(n_4 = 1 \times 10^{10})</td>
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<td>Virtual spin-lattice relaxation time at 4.2 K ((\text{sec})) (Ref. 13)</td>
<td>(\tau_1(1) = 1 \times 10^{-6})</td>
<td>(\tau_1(2) = 7 \times 10^{-6})</td>
<td>(\tau_1(3) = 4 \times 10^{-7})</td>
<td>(\tau_1(4) = 1 \times 10^{-6})</td>
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<tr>
<td>Resistivity at 4.2 K ((\Omega \cdot \text{cm})) ((\Omega \cdot \text{cm})) (Ref. 13)</td>
<td>(\rho_1 = 2 \times 10^3)</td>
<td>(\rho_2 = 5 \times 10^3)</td>
<td>(\rho_3 = 5 \times 10^3)</td>
<td>(\rho_4 = 10^6)</td>
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<tr>
<td>Resistance change induced by ESR at 4.2 K ((\text{Ref. 2-4})) (at (\sim 30 \text{ mW}))</td>
<td>(</td>
<td>\Delta \rho / \rho</td>
<td>_{\text{ESR}} &lt; 10^{-10})</td>
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<tr>
<td>Paramagnetic susceptibility at 4.2 K ((\text{g} / \text{cm}^3)) ((\text{g} / \text{cm}^3)) (Ref. 11)</td>
<td>(\chi_0(1) = 3 \times 10^{-8})</td>
<td>(\chi_0(2) = 2.9 \times 10^{-8})</td>
<td>(\chi_0(3) = 4.6 \times 10^{-8})</td>
<td>(\chi_0(4) = 3.7 \times 10^{-8})</td>
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<td>Thickness of the layer ((\text{nm}))</td>
<td>(t_1 = 9000)</td>
<td>(t_2 = 9000)</td>
<td>(t_3 = 9000)</td>
<td>(t_4 = 9000)</td>
</tr>
<tr>
<td>Resistance of the layer at 4.2 K ((\Omega))</td>
<td>(R_1 = 5 \times 10^6)</td>
<td>(R_2 = 5 \times 10^6)</td>
<td>(R_3 = 5 \times 10^6)</td>
<td>(R_4 = 6 \times 10^6)</td>
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*The values of the upper row and the lower row for \(I\) and \(R\) are those for sample Nos. 2 and 1, respectively.*

\(a\) The values of the upper row and the lower row for \(I\) and \(R\) are those for sample Nos. 2 and 1, respectively.
transferred to and be relaxed at HR because $T_{1_{\text{eff}}'}$ is quite short compared to $\tau_{1}(x_{1})$ at IR. $\Delta \rho/\rho_{\text{ESR}}$ is not observed since most of the absorbed energy is relaxed at HR(II). On the other hand, the Zeeman energy absorbed at LR also tends to flow to HR through IR but, as shown in Fig. 5(a), the energy is relaxed at IR because the thickness of IR is nearly equal to the spin-motion length $[(D_{1}\tau_{1}(x_{1})^{2})]^{1/2}$ at IR for this sample.

Here, $D_{1}$ and $\tau_{1}(x_{1})$ are the spin-motion coefficient and the mean value of $\tau_{1}(x_{1})$ at IR, respectively (see Table I). Therefore, $\Delta \rho/\rho_{\text{ESR}}$ is observed as the broad line which corresponds to the broad ESR signal at LR $5 \times 10^{17} < N_{D} \leq 1.5 \times 10^{20}$ P/cm$^{3}$.

For the ion-implanted Si with 200-keV P and a dose of $3 \times 10^{14}$/cm$^{2}$ (sample No. 2), the block diagram of the relaxation process of the absorbed Zeeman energy is shown in Fig. 5(b). $T_{1_{\text{eff}}'}$ is not very short because HR(II) does not exist. Therefore, HR(II) does not cause the Zeeman energy absorbed at IR to flow to and be relaxed at HR(II). That is, most of the Zeeman energy absorbed at IR and LR is relaxed into the lattice at each region, as shown in Fig. 5(b). Then $\Delta \rho/\rho_{\text{ESR}}$ is observed as the narrow line which corresponds to the narrow ESR signal of IR and HR(II).\textsuperscript{3-4,11,12}

We now make an estimate of the order of magnitudes for $\Delta \rho/\rho_{\text{ESR}}$ on the basis of the model. First, we assume for simplicity that each of the four layers ([i.e., HR(II), HR(I), IR, and LR] in Fig. 1 contains a constant donor concentration $n_{i}$ and has a mean value of other physical quantities as shown in Table I. Since resistance changes at LR can be neglected due to $R_{4} \approx R_{1}$ and $R_{3}$, the resistance change $\Delta \rho/\rho_{\text{ESR}}$ of the total layers is

$$\frac{\Delta \rho}{\rho} \bigg|_{\text{ESR}} \text{(calc)} = \frac{\Delta R_{4}}{R_{4}} \bigg|_{\text{ESR}} = \frac{R_{2}R_{3}A}{R_{1}} \frac{\Delta R_{1}}{R_{1}} \bigg|_{\text{ESR}} + \frac{R_{2}R_{3}A}{R_{2}} \frac{\Delta R_{2}}{R_{2}} \bigg|_{\text{ESR}} + \frac{R_{2}R_{3}A}{R_{3}} \frac{\Delta R_{3}}{R_{3}} \bigg|_{\text{ESR}},$$

where $R_{i}' = R_{i} + R_{2}A + R_{3}A + R_{2}R_{3}A + R_{2}R_{3}A$, and $A = R_{4}R_{2} + R_{3}R_{2} + R_{4}R_{3}A + R_{2}R_{3}A$. The resistance change of each layer is

$$\Delta R_{i}/R_{i} \bigg|_{\text{ESR}} = a_{i} \rho[HR(II)],$$

$$\Delta R_{i}/R_{i} \bigg|_{\text{ESR}} = a_{i} \rho[HR(I)],$$

$$\Delta R_{i}/R_{i} \bigg|_{\text{ESR}} = a_{i} \rho[IR],$$

where $\rho[HR(II)], \rho[HR(I)],$ and $\rho[IR]$ are the power relaxed at HR(II), HR(I), and IR, respectively, and $a_{1}, a_{2},$ and $a_{3}$ are the conversion constants ($a_{1} \approx a_{2} >> a_{3}$). The first term in Eq. (3) can be neglected since $\Delta R_{i}/R_{i} \bigg|_{\text{ESR}} \leq 10^{-9}$.\textsuperscript{1,4}

For sample No. 2, the second and third terms in Eq. (3) are of the same order of $5 \times 10^{-7}$ and $8 \times 10^{-7}$, respectively, if we assume no energy transfer from IR to HR(I). The value of $1.3 \times 10^{-6}$ is smaller than the observed value of $\Delta \rho/\rho_{\text{ESR}}$ of $5 \times 10^{-6}$. However, this difference seems to be due to the oversimplified approximation of four layers and due to the enhanced diffusion (i.e., $l_{2}$ and $l_{3}$ become larger).

Assuming that, for sample No. 1, HR(II), HR(I), and IR make one metallic system where there is fast energy transfer, the ratio of the power, $\rho[HRII], \rho[HR(I)],$ and $\rho[IR]$, absorbed at each layer and of the power relaxed at each layer is

$$\rho[HR(II)]; \rho[HR(I)]; \rho[IR] = 1:0.88:0.70,$$

$$\rho[HR(II)]; \rho[HR(I)]; \rho[IR] = 1:0.029:0.00083$$

by calculating from Table I. It is found that most of absorbed energy is relaxed at HR(II) and that the second and third term in Eq. (3) are extremely small. However, the third term in Eq. (3) becomes dominant due to the energy transfer from LR to IR. We assume that the transferred energies are all relaxed at IR as shown in Fig. 5(a). The power transferred and relaxed at IR is

$$\rho[IR] \doteq \rho[LR],$$

$$\rho[IR] \doteq \rho[LR]\frac{\chi_{0}(4)H_{0}^{2}}{\tau_{1}(4)} \frac{\gamma^{2}H_{0}^{2} \tau_{1}(4) \tau_{1}(4)}{1 + \gamma^{2}H_{0}^{2} \tau_{1}(4) \tau_{1}(4)},$$

where $\chi(4)$ is the paramagnetic susceptibility at LR, $\gamma$ is the gyromagnetic ratio, $\tau_{1}(4)$ is the virtual spin-spin relaxation time at LR, $H_{0}$ is the static magnetic field at resonance, and $H_{1}$ is the oscillating magnetic field. With use of the values in Table I and $\tau_{1}(4) = 5 \times 10^{-8}$ sec, $H_{1} = 0.25$ G, $H_{0} = 3200$ G, and $\chi_{0}(4)$ at $1.6$ K is $7.1 \times 10^{-8}$ cgs/g/11 in Eq. (6) is estimated as follows:

$$\Delta R_{4}/R_{4} \bigg|_{\text{ESR}} = a_{4} \rho[IR],$$

$$= 8.6 \times 10^{-7} a_{4},$$

Here, $a_{4} = (a_{1} \eta) \theta$ in Ref. 3 and we put $\theta = 1.4$ (cm$^{3}$/W) and $\eta = 0.25$ at 1.6 K as an averaged value; i.e., $a_{3} = 3.5 \times 10^{4}$ (cm$^{2}$/W). Therefore, we have

$$\Delta \rho/\rho_{\text{ESR}}(\text{calc}) = \frac{R_{1}R_{4}}{A} \frac{\Delta R_{4}}{R_{4}} \bigg|_{\text{ESR}} = 1.8 \times 10^{-7}$$

for the broad line of sample No. 1 at 1.6 K. This is smaller than the observed value of $\Delta \rho/\rho_{\text{ESR}}$ of $7 \times 10^{-7}$. However, we think that the agreement on the order of magnitude between the calculation on the basis of the model and experiment is reasonable, in spite of the ambiguity of the value in Table I and that of $\alpha$.

Finally, we consider that the broad line of $\Delta \rho/\rho_{\text{ESR}}$ is not due to the bolometric effect,\textsuperscript{5} because the energy relaxed at HR(II) has no effects on $\Delta \rho/\rho_{\text{ESR}}$, and because the broad line has not been observed in bulk Si : P with much more spins. The broad line is not due to the Q-loss effect\textsuperscript{6} because the linewidth of $\Delta \rho/\rho_{\text{ESR}}$ does not agree with that of ESR. Furthermore, the narrow line also does not seem to be due to these effects.

V. CONCLUSION

We have observed for the first time the ESR-induced changes in the dc resistance, $\Delta \rho/\rho_{\text{ESR}}$ of P-ion-implanted Si. A new broad line which cannot be detected by the usual ESR can be detected by this $\Delta \rho/\rho_{\text{ESR}}$ method. The origin and the mechanism of the new broad line are well explained in terms of the energy-transfer model; i.e., the broad line originates from the ESR of the localized donors at LR and from the transfer of the Zeeman energy absorbed there to IR where the resis-
tance changes take place. The transfer is caused by the existence of HR(II) which acts as a Zeeman energy absorber. This interesting phenomenon has first been observed in the ion-implanted Si:P system but may be expected in other systems which have an impurity distribution within the thin surface layer.

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7N_{e} was determined by assuming uniform distribution over 2R_{p} since the states of donor electrons are different between LHeT and 77 K. See K. Murakami, K. Masuda, and S. Namba, Solid State Commun. 18, 663 (1976).